

k-Space Associates, Inc.



In-Line Process Monitoring

for CIGS, CdTe, CIS, & Silicon PV Materials

Glass Panel

> Flexible Substrate

Today's **solar power generation industry** is quickly evolving with a new breed of compound semiconductor materials

leading the charge. These new, thin-film based materials have already surpassed performance requirements needed for global deployment. However, mass production and yield problems have limited broad commercialization of these promising thin-film PV materials. A key factor in producing the highest efficiency cells at the lowest cost will be the successful deployment of automated high-volume production with tight process control. To achieve this goal, it is essential that monitoring methodologies be implemented for higher conversion

"Measure Optical Properties in Real-Time to Increase Yield and Performance" efficiency and reduced manufacturing costs. This includes implementing in-line metrology tools that monitor the performance metrics of the thin-film photovoltaic materials being produced so that the manufacturing and optimized in real time

process variables can be controlled and optimized in real-time.

k-Space has directly addressed this important in-line metrology need with our kSA BandiT PV system. This revolutionary system directly measures key parameters such as surface roughness, layer thickness, optical band gap, temperature, and other thin-film properties critical to PV device performance. kSA BandiT PV spectrally analyzes diffusely reflected light via solid state electronics to enable measurements over a wide spectral range. Modular designs and flexible geometries allow for rapid measurement at multiple locations across either glass panel or flexible substrate processing lines.







Performance Specifications

| Optical Property | Parameter Range | Accuracy | Run to Run and Tool to Tool Repeatability |
|--|----------------------------|----------|---|
| Optical Band Gap | 425-1725 nm (0.7-2.9eV) | +/- 1 | +/- 0.15 |
| Metal Film/Substrate Temperature | 250-1000 (°C) | +/- 2 | +/- 1 |
| Semiconductor Film/ Substrate Temperature | RT-700 (°C) | +/- 2 | +/- 1 |
| Film Thickness | 1-4 (um) | +/- 0.1 | +/- 0.1 |
| Film Roughness | >0.1% Change | NA | NA |

Options

| Jnit # | Description |
|----------|---|
| 3-NIR-PV | Spectrometer and optics tailored for CIGS and Silicon PV material spectral analysis in the range of 920-1720 nm. |
| 3-VIS-PV | Spectrometer and optics tailored for PV material spectral analysis in the range of 340-940 nm for CdS, CIS, and CdTe related materials. |
| 3-PV-MP | Multiple spectrometer and optical head package. Allows for up to 4 simultaneous kSA BandiT PV measurements at multiple locations across panel/web for process uniformity analysis. |
| 3-PV-SD | Linear scanning stage, optical head, and software for up to 300 mm of travel across panel/web. Provides access to any discrete sampling location for process uniformity analysis. |
| 3-PV-AOS | Offline data analysis software key. |